

# **ELEN E3106/4106 Lecture 15**

## **Introduction to BJTs**

### **Outline**

- Qualitative overview
- Theory of operation
- Energy band diagrams
- Electrostatics in Equilibrium

#### **Assignments:**

Reading: Streetman and Banerjee §7.1-7.2

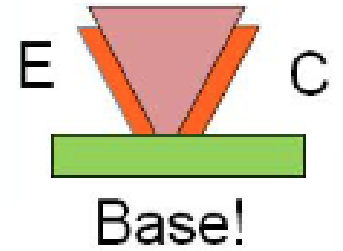
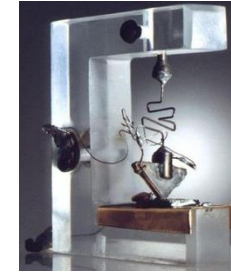
Exam 2 this Tuesday Oct. 28<sup>th</sup> during class

# BJT Intro

- **B** \_\_\_\_\_ **J** \_\_\_\_\_ **T** \_\_\_\_\_
  - Bipolar: both \_\_\_\_\_ and \_\_\_\_\_ involved
  - Junction: p-n junctions are critical to its operation!

## What do transistors do?

1. **Amplification:** a \_\_\_\_\_ signal (I or V, terminal #2) can \_\_\_\_\_ (usually I, flowing between terminal #1 and #3)
  - Think of a \_\_\_\_\_ controlling the amount of \_\_\_\_\_ through a giant hose!
2. **Switching:** the transistor can be turned \_\_\_\_\_
  - Two main types of transistors studied in E3106/4106:
    - 1) BJT: small input current (faucet) controls large output current (hose) e.g. \_\_\_\_\_
    - 2) Next unit: Field effect transistors (FET): small input voltage (faucet) controls large output current (hose) e.g. \_\_\_\_\_

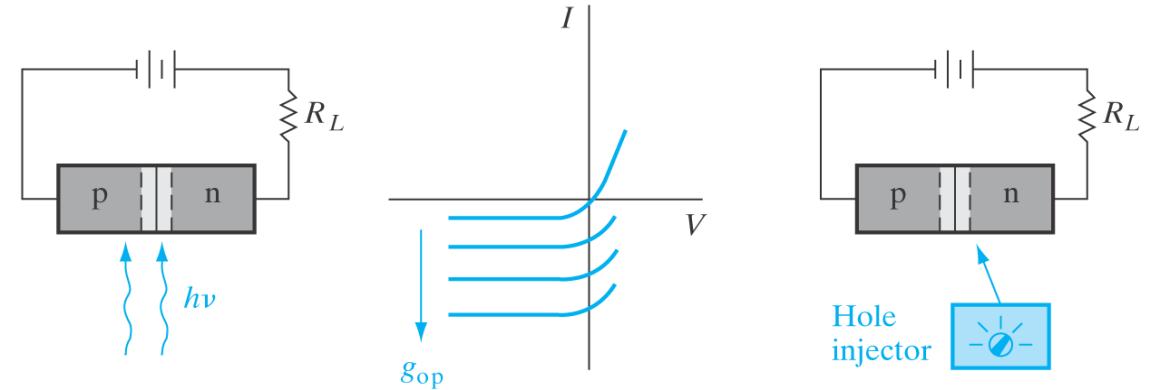


1947

Invention of the 1<sup>st</sup> transistor (Ge point contact)  
*Shockley, Bardeen, Brattain*  
*Bell Labs*

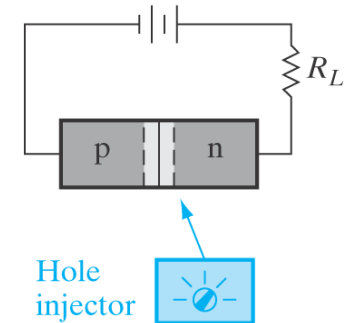
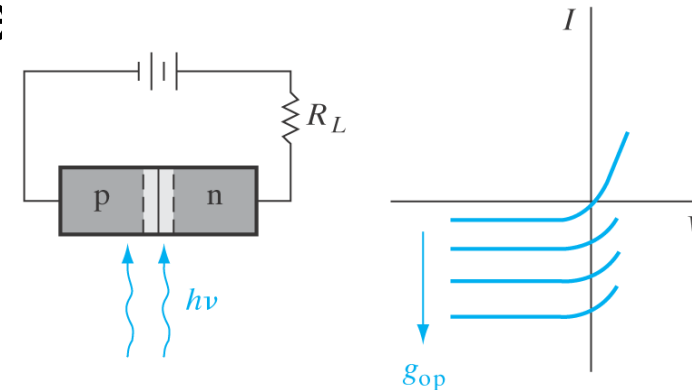
## BJT Advantages and Recap of p-n Diode

- Disadvantage: Current-controlled current sources always have some current flowing (\_\_\_\_\_)
  - Limits \_\_\_\_\_ per chip
  - This is where FETs have an advantage
- BJTs have gradually been replaced by CMOS in the past 30 years, especially for high-speed logic
- But, BJTs are better for have \_\_\_\_\_ and \_\_\_\_\_
  - Better for \_\_\_\_\_ circuits
- p-n diode with the lights on
  - Recall: In RB, the current with the lights off was *small* (\_\_\_\_\_)
- When light is on, it creates EHPs in the \_\_\_\_\_. Assuming L.L. injection, minority carriers are easily \_\_\_\_\_ by the E-field and injected into the other side, modulating the current.



# BJT Principle of Operation

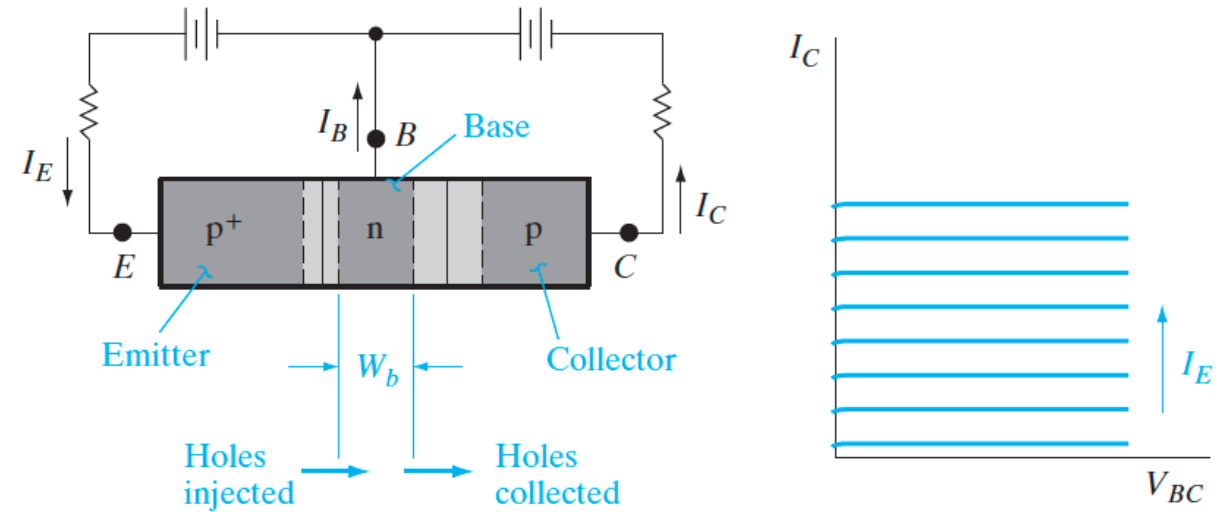
- Takeaway of RB p-n diode under illumination: we can \_\_\_\_\_ the reverse current through the diode by \_\_\_\_\_ the rate of EHP generation!
- Question: Is it possible to inject \_\_\_\_\_ into the neighborhood of the junction electrically instead of optically?
- \_\_\_\_\_! Consider a “hole injection device
- If we can inject \_\_\_\_\_ into n side, current will resemble optical generation effects
  - Current from n to p will depend on rate of injection and **not** \_\_\_\_\_
- What happens to the current if we increase the external load,  $R_L$ ?



# BJT Principle of Operation

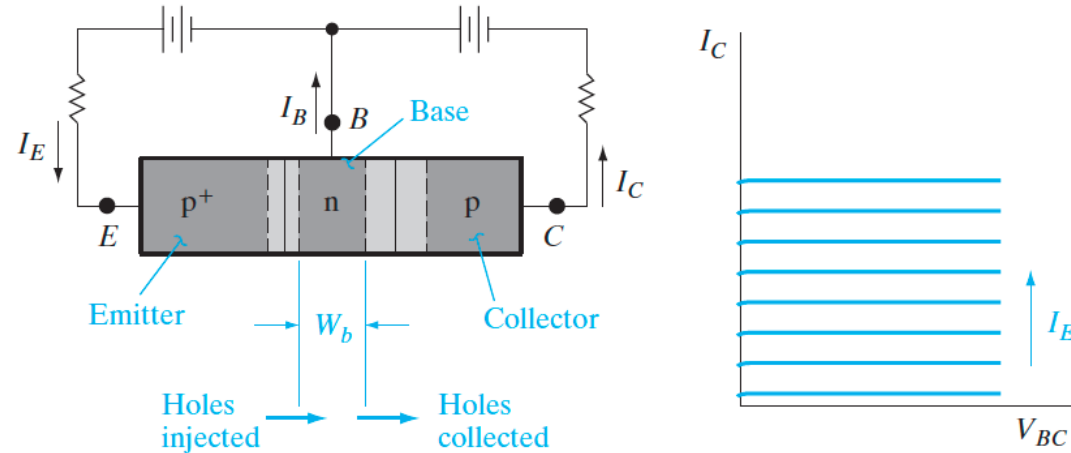
- What would be a convenient hole injection device?
  - A \_\_\_\_\_ p<sup>+</sup>-n junction!
  - Recall: current due primarily to \_\_\_\_\_ injected from p<sup>+</sup> side into the n material
- If we make the \_\_\_\_\_ of the RB p-n junction the same as the n-side of the FB p<sup>+</sup>-n junction, we have a \_\_\_\_\_ BJT!
  - A BJT is basically \_\_\_\_\_ p-n junctions

*Common base configuration: base electrode B is common to the emitter and collector circuits.*



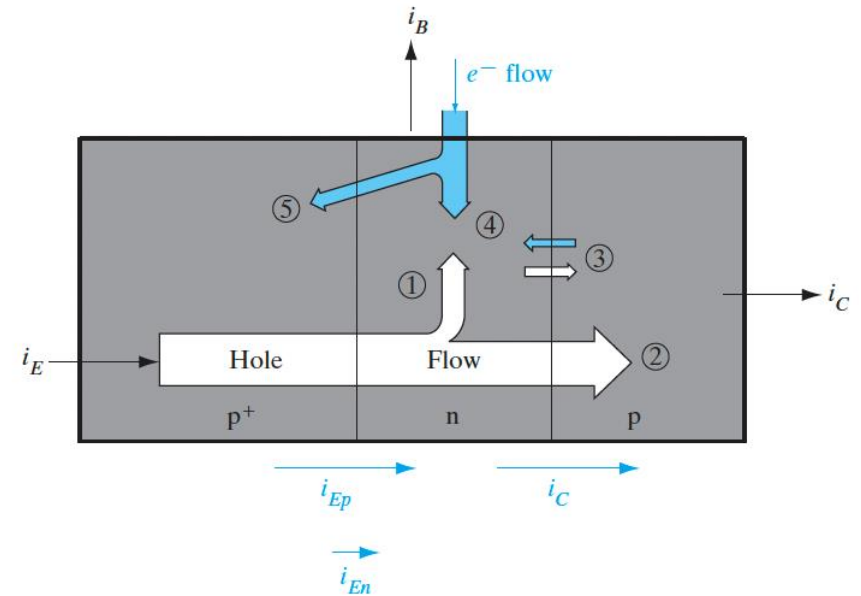
pnp BJT with FB emitter and RB collector and the I-V characteristics of the RB n-p junction (collector) as a function of emitter current.

# BJT Requirements for Efficient Hole Collection



- \_\_\_\_\_ (\_\_\_\_\_ junction ) injects h<sup>+</sup> into RB base-collector
- Requirement: For \_\_\_\_\_ to collect most holes, the n base region \_\_\_\_\_ must be \_\_\_\_\_ compared to the hole diffusion length so carriers don't \_\_\_\_\_ before reaching collector!  $W_b \ll \underline{\hspace{1cm}}$  (we called this a \_\_\_\_\_ diode!)
  - Recall:  $L_p = \sqrt{D_p \tau_p}$
- If so, when BJT is biased \_\_\_\_\_ then almost all injected holes are collected:
- $I_E \approx \underline{\hspace{1cm}}$  are the “large” currents here (water passing through the hose)

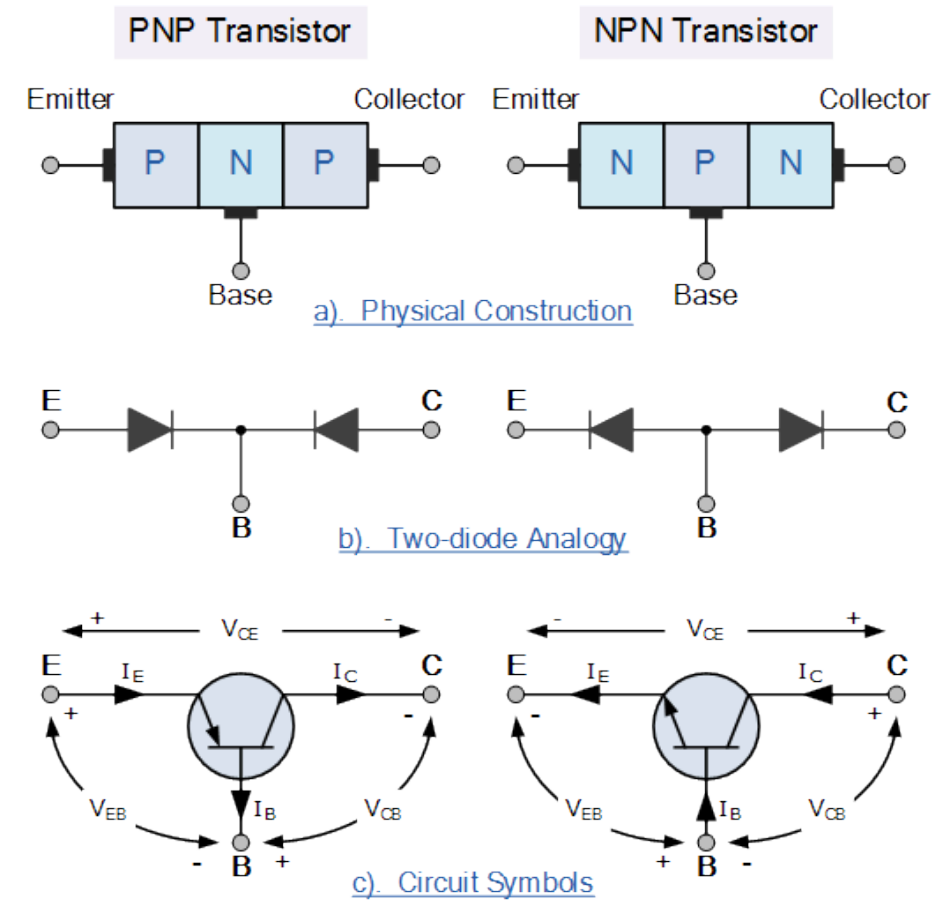
# BJT Base Current



- But is there a base current \_\_\_\_? Why?
- Recall: base is \_\_-type in pnp
  - Some e<sup>-</sup> in the base will \_\_\_\_\_ with injected holes
  - Some e<sup>-</sup> will be \_\_\_\_\_ from n to p<sup>+</sup> in the FB emitter junction
  - Some \_\_\_\_\_ e<sup>-</sup> from collector are swept into base at the RB collector junction (reduces  $I_B$ )
- Ideally,  $I_B$  is very \_\_\_\_\_ so  $I_E \approx I_C$
- In properly designed BJT,  $I_C = I_E - I_B$  where  $I_E \approx$  \_\_\_\_\_  $I_B$

# BJT Symbols and Conventions

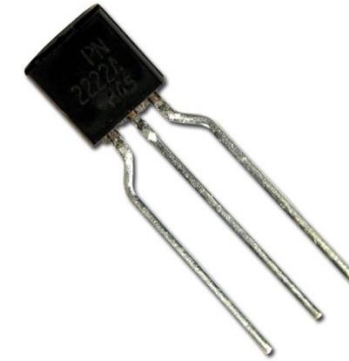
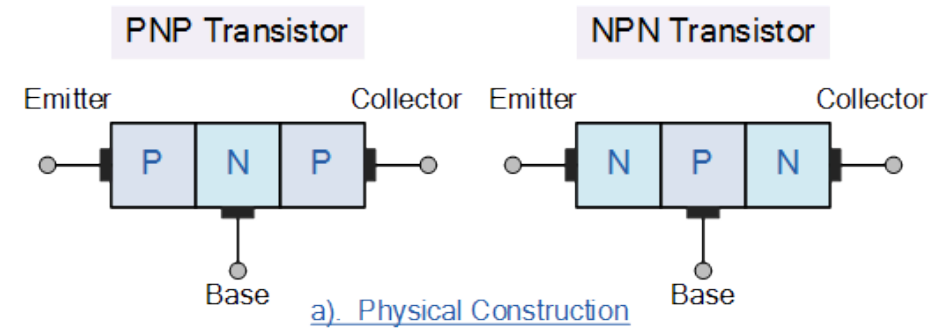
- Why does direction of arrow in symbol note?
- In pnp, current flows \_\_\_\_\_ from the emitter
- In npn, current flows \_\_\_\_\_ from the emitter
- Easier to study pnp because current flows in direction of \_\_\_\_\_
- But npn is similar, we can just reverse the roles of  $e^-$  and  $h^+$  from our pnp discussion
- Which is faster? Why?





# Transistor Terminals

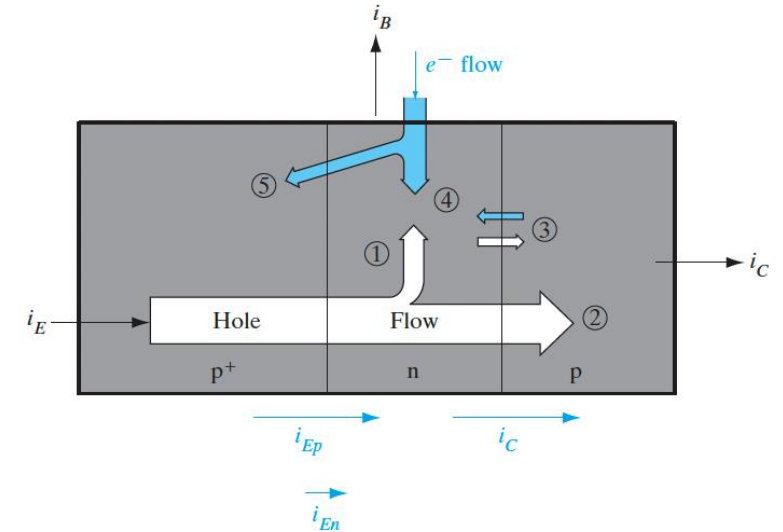
- Terminal: Any externally available point of \_\_\_\_\_ (M-S contact)
- Recall: M-S contacts can be thought of as infinite carrier sources/sinks
- How many terminals does a transistor have? \_\_\_\_\_
- Terminal 1: brings current into the transistor
  - BJT: \_\_\_\_\_, MOSFET: \_\_\_\_\_
- Terminal 2: carries current out
  - BJT: Collector, MOSFET: \_\_\_\_\_
- Terminal 3: acts as a handle to control the current flow (input terminal)
  - BJT: Base, MOSFET: \_\_\_\_\_



Sources: [https://www.electronics-tutorials.ws/transistor/tran\\_1.html](https://www.electronics-tutorials.ws/transistor/tran_1.html), Amazon

## BJT Simple Analysis: Performance Parameters

- Base transport factor:  $B = I_C / I_{E, \text{majority}}$ 
  - Fraction of h+ which make it across the \_\_\_\_\_ to \_\_\_\_\_
- Emitter injection efficiency:  $\gamma = \frac{I_{E, \text{majority}}}{I_{E, \text{majority}} + I_{E, \text{minority}}}$ 
  - Ratio of current due to h+ to \_\_\_\_\_ current
- Current transfer ratio:  $\alpha = B\gamma = \frac{BI_{E, \text{majority}}}{I_{E, \text{majority}} + I_{E, \text{minority}}} = \frac{I_C}{I_E} = \frac{B}{1+B}$ 
  - Represents the emitter-to-collector current \_\_\_\_\_
- Base-to-collector current \_\_\_\_\_ factor:  $\beta = \frac{I_C}{I_B} = \frac{B\gamma}{1-B\gamma} = \frac{\alpha}{1-\alpha}$
- Applies to DC and small-signal AC (\_\_\_\_\_) operation
- We are assuming no \_\_\_\_\_ in the SCRs
- What have we found?  $I_C$  is controlled by \_\_\_\_\_!
- A small increase in \_\_\_\_\_ results in a much larger increase in \_\_\_\_\_. The transistor amplifies the small base current into a much larger collector current, which is why BJTs are used as current amplifiers!
- \_\_\_\_\_ is related to both the base current and the collector current but is not the controlling factor in BJT behavior. Instead, it is the sum of the two currents and is slightly larger than \_\_\_\_\_!



# BJT Band Diagram

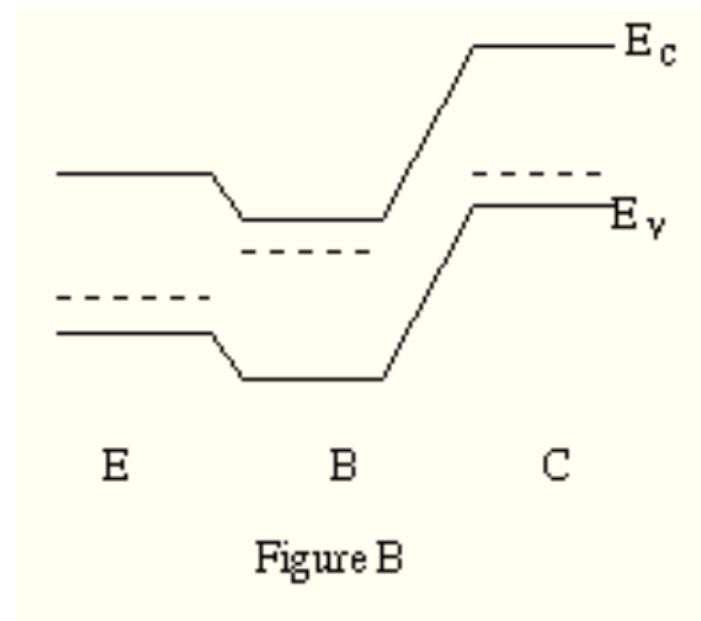
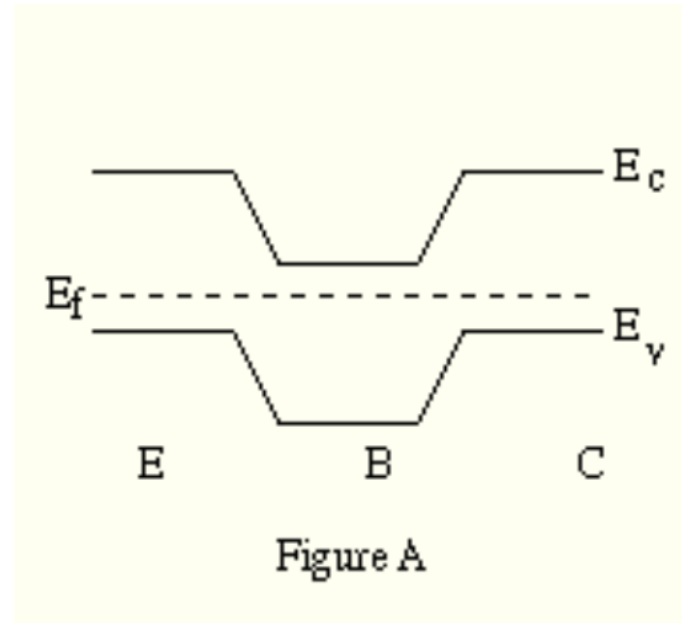
npn:

- In equilibrium:

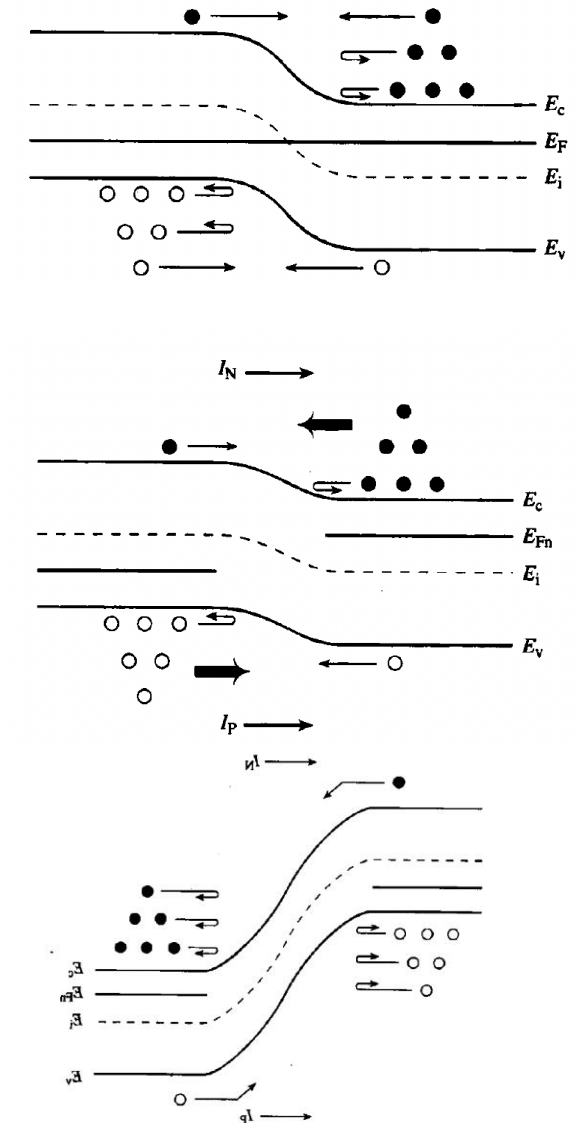
- In “\_\_\_\_\_” mode:

- E-B junction: *Forward biased*
  - Recall, rate of injection  $\propto$  \_\_\_\_\_
- C-B junction: *Reverse biased*

$$I = I_0(e^{qV/kT} - 1)$$



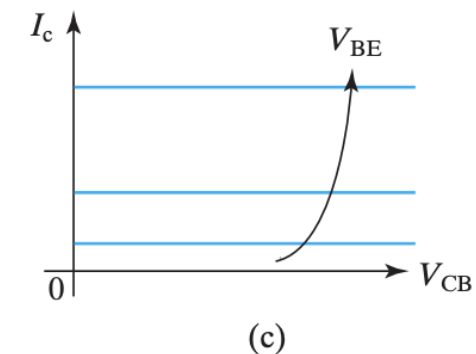
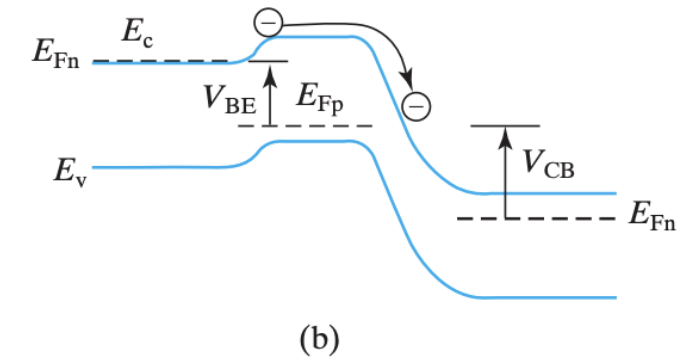
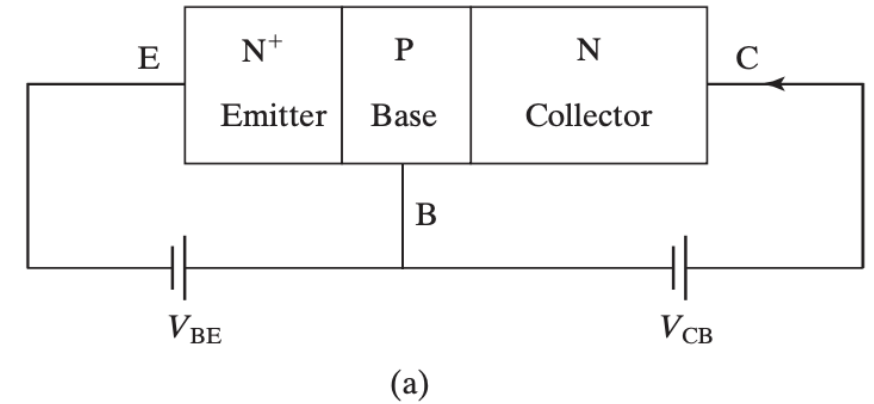
Recall our equilibrium, FB, and RB diagrams for a **single** p-n junction:



# BJT Band Diagram

npn in “normal” mode:

- When the base–emitter junction is FB, e- are injected into the \_\_\_\_\_ base
- e- \_\_\_\_\_ across the narrow base to RB base–collector junction, reach edge of the \_\_\_\_\_, and get swept into the collector
- $I_C$  is essentially independent of  $V_{CB}$ , as long as  $V_{CB}$  is \_\_\_\_ (or small FB)
- $I_C$  is instead determined by rate of e- injection from the \_\_\_\_\_ (e.g.  $V_{BE}$  and \_\_\_\_\_)



# BJT “Big Three”

- Let's again consider the BJT as two independent p-n junctions
- In equilibrium
  - Electrostatic potential:
  - Electric field:
  - Charge density:
- In this example,  $N_a \gg N_{d,B} > N_{a,C}$

